Semiconductor Device Set - Page 1 of 1



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Inclosure Materia	l:
Plastic all transisto	r
Overall Length:	
0.185 inches all tra	ansistor
Terminal Length:	
0.500 inches all tra	ansistor
Internal Configura	ation:
Field effect all trans	sistor
Channel Polarity	And Control Type (non-core):
N-channel junction	type all transistor
Component Func	tion Relationship:
Matched	
Component Name	e And Quantity:
4 transistor	
Mounting Method	:
Terminal all transis	stor
Field Force Effect	а Туре:
Electrostatic charg	e
Features Provide	d:
Hermetically sealed	d case and electrostatic sensitive
Semiconductor M	aterial:
Silicon all transisto	r
Voltage Rating In	Volts Per Characteristic:
25.0 drain to gate	voltage all transistor and 25.0 drain to source voltage all transistor and 25.0 reverse gate to source voltage all transistor
Current Rating Pe	er Characteristic:
10.00 milliamperes	s zero-gate-voltage source current horsepower metric all transistor
Power Rating Per	Characteristic:
625.0 milliwatts sm	nall-signal input power, common-collector absolute all transistor
Maximum Operati	ing Tempurature Per Measurement Point:
150.0 degrees cels	sius junction all transistor
Terminal Type An	Id Quantity:
12 uninsulated wire	e lead all transistor
Shelf Life:	
N/a	
Unit Of Measure:	
Demilitarization:	
No	
Fiig:	
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